

THIN FILM DUAL RESISTOR NETWORKS

MSDR 3 SERIES

The MSDR series dual center-tapped chip resistor offers the high stability, low noise, and low T.C.R./T.C. tracking of thin film while providing greater flexibility in hybrid designs.

MECHANICAL DATA

SIZE	0.030" x 0.030" x 0.010" (± 0.003 ")
SUBSTRATE	SILICON, ALUMINA, QUARTZ, OR GLASS
RESISTOR	NICHROME OR TANTALUM NITRIDE
BOND PADS	15K Å MINIMUM GOLD STD.; ALUMINUM AVAILABLE
BACKSIDE SURFACE	BARE SUBSTRATE; GOLD BACK OPTIONAL

ELECTRICAL DATA

RESISTANCE RANGE	VALUES FROM 1 Ω TO 1M Ω PER SIDE; CONSULT SALES FOR SPECIFIC COMBINATIONS OR FOR HIGHER VALUES
TOLERANCES	0.01%, 0.02%, 0.05%, 0.1%, 0.25%, 0.5%, 1%, 2%, 5%, 10% (R1 & R2 trimmed to absolute tolerance when total tolerance <0.100 Ω) R1 & R2 TRIMMED TO ABSOLUTE MINIMUM
CENTER TAP RATIO T.C.R.	$\pm 1\%$ STD.; AVAIL. TO $\pm 0.01\%$ NICHROME: ± 50 ppm STD.; ± 25 ppm, ± 10 ppm, ± 5 ppm OPTIONAL TANTALUM NITRIDE : ± 100 ppm STD.; ± 50 ppm, ± 25 ppm, ± 10 ppm OPTIONAL
T.C. TRACKING	TO ± 2 ppm/ $^{\circ}$ C; VALUE DEPENDENT

SERIES DATA

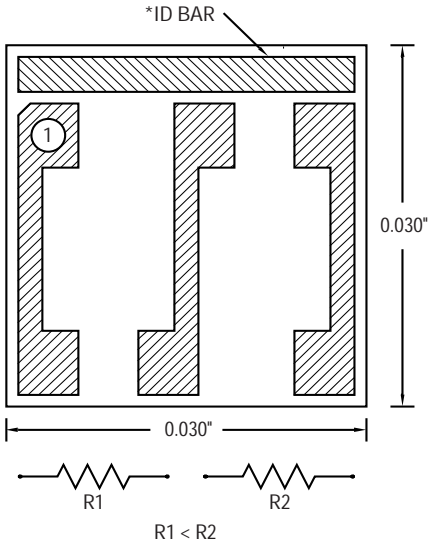
CURRENT NOISE	-20dB TYPICAL
DIELECTRIC BREAKDOWN	400 V MIN.
INSULATION RESISTANCE	10 ¹² Ω MIN.
OPERATING VOLTAGE	100 V MAX.
POWER RATING	250 mW TOTAL (70 $^{\circ}$ C DERATED LINEARLY TO 150 $^{\circ}$ C). P = E ² /R 50 mW TOTAL (70 $^{\circ}$ C DERATED LINEARLY TO 150 $^{\circ}$ C). P = E ² /R
SHORT TIME OVERLOAD	5X RATED POWER, 25 $^{\circ}$ C, 5 SEC., $\pm 0.25\%$ MAX. $\Delta R/R$: 0.1% MSI TYPICAL
HIGH TEMP. EXPOSURE	150 $^{\circ}$ C, 100 HRS., $\pm 0.25\%$ MAX. $\Delta R/R$: 0.03% MSI TYPICAL
THERMAL SHOCK	MIL-STD 202, METHOD 107F, $\pm 0.25\%$ MAX. $\Delta R/R$: 0.1% MSI TYPICAL
MOISTURE RESISTANCE	MIL-STD 202, METHOD 106, $\pm 0.5\%$ MAX. $\Delta R/R$: 0.1% MSI TYPICAL
STABILITY	1000 HRS., 70 $^{\circ}$ C, 125mW, $\pm 0.5\%$ MAX. $\Delta R/R$: 0.1% MSI TYPICAL
OPERATING TEMP. RANGE	-55 $^{\circ}$ C TO +125 $^{\circ}$ C
STABILITY RATIO	0.1% MAX. $\Delta R/R$ STANDARD: 0.05% MAX. $\Delta R/R$ OPTIONAL;
FREQUENCY	TO 20 GHz (RESISTOR GEOMETRY DEPENDENT)
STRAY DISTRIBUTED CAPACITANCE	
SILICON / NiCr OR TaN	2pF
ALUMINA / NiCr	0.06pF
ALUMINA / TaN	0.08pF
QUARTZ / NiCr	0.02pF
QUARTZ / TaN	0.05pF
GLASS / NiCr	0.04pF
GLASS / TaN	0.06pF

PART NUMBER DESIGNATION

MSDR 3	X	X	XXXXX / XXXXX	X/X	X
SERIES	SUBSTRATE	RESISTIVE FILM	OHMIC CODES R1 / R2	TOLERANCE CODES	OPTION DESIGNATOR
			5-Digit Number: 1st 4 Digits Are Significant With "R" As Decimal Point When required. 5th Digit Represents Number of Zeros.	R1 < R2 S = 0.01% X = 0.02% Q = 0.05% B = 0.1% C = 0.25% D = 0.5% F = 1% G = 2% J = 5% K = 10%	(If Required) A = ± 50 ppm/ $^{\circ}$ C B = ± 25 ppm/ $^{\circ}$ C C = ± 10 ppm/ $^{\circ}$ C D = ± 5 ppm/ $^{\circ}$ C E = Aluminum Bond Pads F = ± 100 ppm/ $^{\circ}$ C **G = Gold Bond Pads GB = Gold Backside RB = 0.05% RATIO RC = 0.1% RATIO RD = 0.5% RATIO **Std. if no other option required.

EXAMPLES: MSDR 3ST-300R0B/500R0B-A = Silicon/Tantalum Nitride with R1 = 300 Ω ; R2 = 500 Ω , $\pm 0.1\%$ Tol., ± 50 ppm/ $^{\circ}$ C T.C.R., with Gold Bond Pads

* PART MARKING AVAILABLE, CONSULT SALES.



NOTCHED PAD INDICATES LOCATION OF R1

MSI
MINI-SYSTEMS, INC.
THIN FILM DIVISION

45 FRANK MOSSBERG DRIVE, ATTLEBORO, MA 02703
508-226-2111 FAX: 508-226-2211

DCN TF 108-D-1197